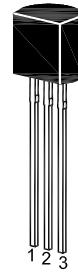


2SB1116 / 2SB1116A

PNP Silicon Epitaxial Planar Transistor

Audio frequency power amplifier and medium speed switching.

The transistor is subdivided into three groups, Y, G and L, according to its DC current gain.



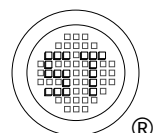
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60 80	V
Collector Emitter Voltage	$-V_{CEO}$	50 60	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$	1	A
Collector Current (Pulse)	$-I_{CP}$	2	A
Power Dissipation	P_{tot}	0.75	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 0.1\text{ A}$	h_{FE}	135	270	-
	h_{FE}	200	400	-
	h_{FE}	300	600	-
at $-V_{CE} = 2\text{ V}$, $-I_C = 1\text{ A}$	h_{FE}	81	-	-
Collector Base Cutoff Current at $-V_{CB} = 60\text{ V}$	$-I_{CBO}$	-	100	nA
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	100	nA
Collector Emitter Saturation Voltage at $-I_C = 1\text{ A}$, $-I_B = 50\text{ mA}$	$-V_{CE(sat)}$	-	0.4	V
Base Emitter Saturation Voltage at $-I_C = 1\text{ A}$, $-I_B = 50\text{ mA}$	$-V_{BE(sat)}$	-	1.2	V
Base Emitter On Voltage at $-V_{CE} = 2\text{ V}$, $-I_C = 50\text{ mA}$	$-V_{BE(on)}$	0.6	0.7	V
Gain Bandwidth Product at $-V_{CE} = 2\text{ V}$, $-I_C = 100\text{ mA}$	f_T	70	-	MHz



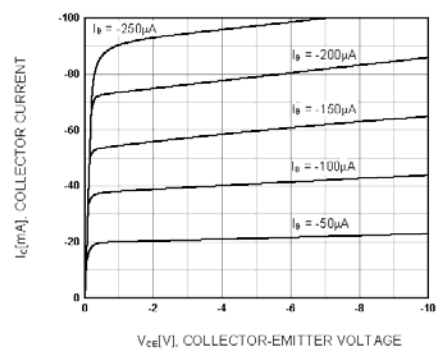


Figure 1. Static Characteristic

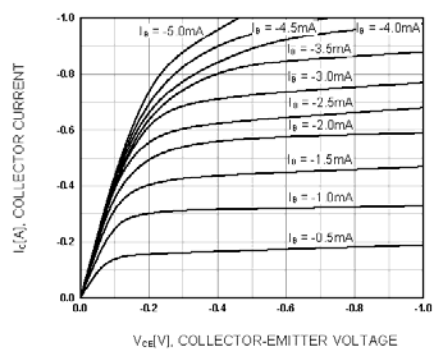


Figure 2. Static Characteristic

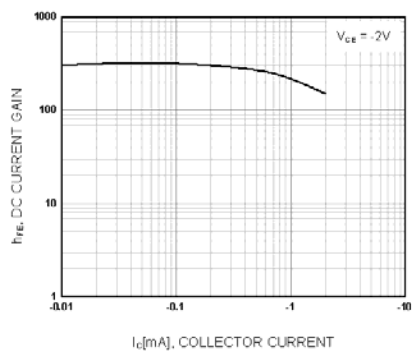


Figure 3. DC current Gain

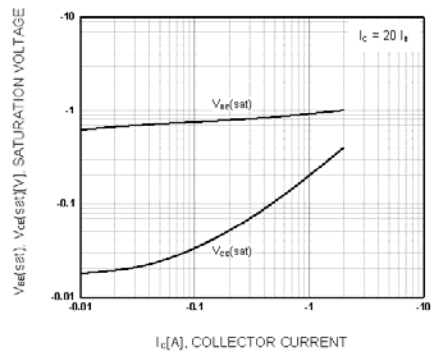


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

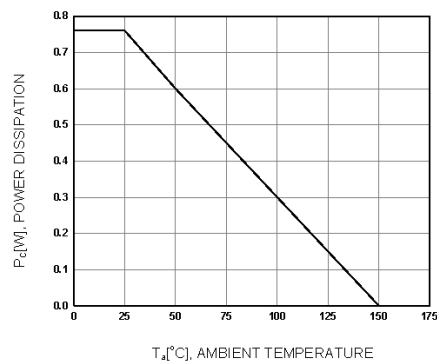


Figure 5. Power Derating

